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(12) United States Design Patent

Vinciarelli et al.

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(54) **SEMICONDUCTOR DEVICE**

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(**) Term: **14 Years**

(21) Appl. No.: **29/448,057**

(22) Filed: **Mar. 8, 2013**

Related U.S. Application Data

(63) Continuation-in-part of application No. 13/789,065, filed on Mar. 7, 2013.

(51) **LOC (10) Cl.** **13-03**

(52) **U.S. Cl.**
USPC **D13/182**

(58) **Field of Classification Search**
USPC D13/110, 182; 257/668, 678, 690; 361/679.01, 713, 728, 736, 760, 761, 361/775, 820; 324/71.5, 252; 174/250, 253; 438/64, 65, 66
See application file for complete search history.

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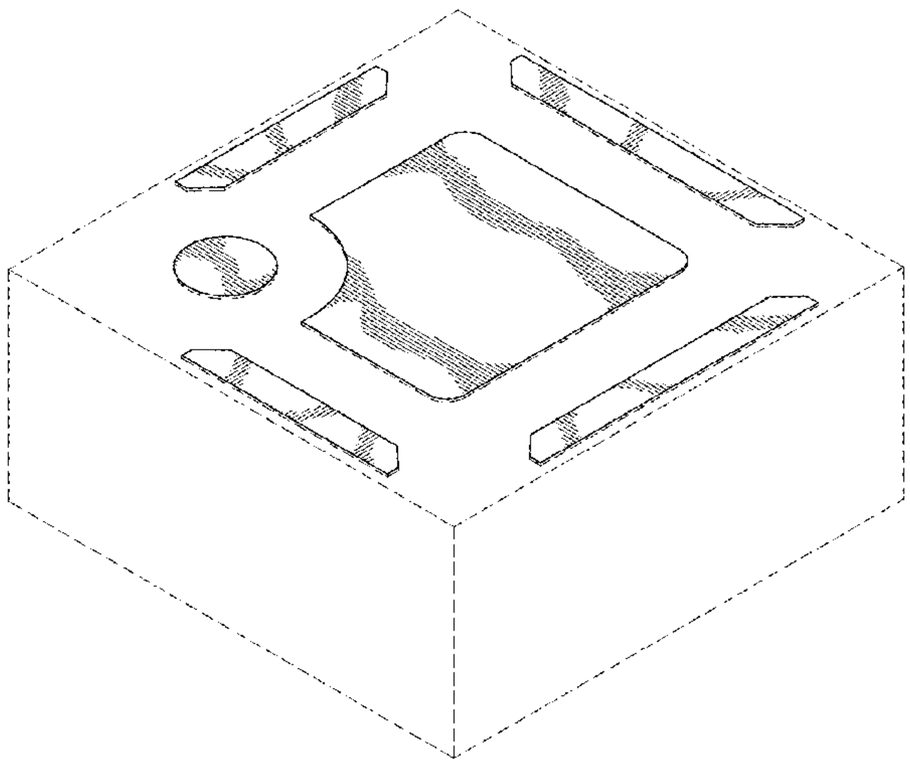
(57) **CLAIM**

We claim the ornamental design for a semiconductor device, as shown and described.

DESCRIPTION

FIG. **1** is a perspective view of a first embodiment of a semiconductor device showing our new design;
FIG. **2** is a top plan view thereof;
FIG. **3** is a bottom plan view thereof;
FIG. **4** is a front elevation view thereof;
FIG. **5** is a rear elevation view thereof;
FIG. **6** is a right side elevation view thereof;
FIG. **7** is a left side elevation view thereof;
FIG. **8** is a perspective view of a second embodiment of a semiconductor device showing our new design;
FIG. **9** is a top plan view thereof;
FIG. **10** is a bottom plan view thereof;
FIG. **11** is a front elevation view thereof;
FIG. **12** is a rear elevation view thereof;
FIG. **13** is a right side elevation view thereof; and,
FIG. **14** is a left side elevation view thereof.
The broken lines shown in the drawings represent portions of the semiconductor device that form no part of the claimed design.

1 Claim, 10 Drawing Sheets



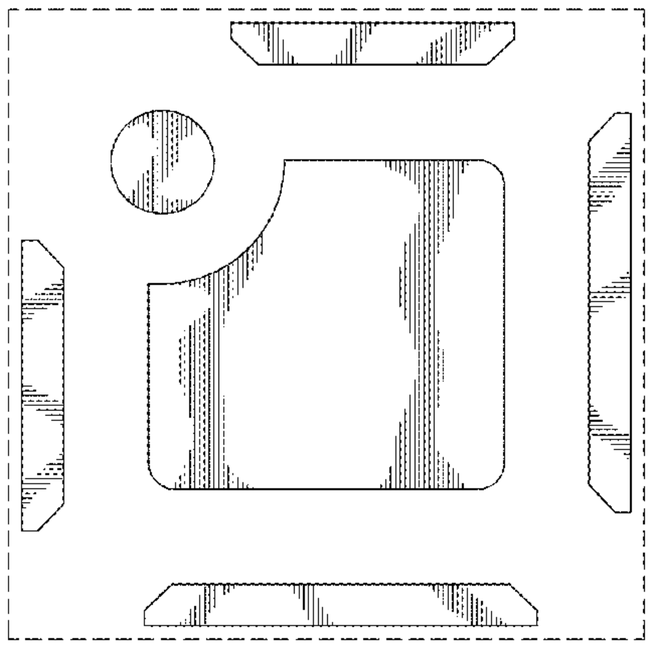


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Fig. 1

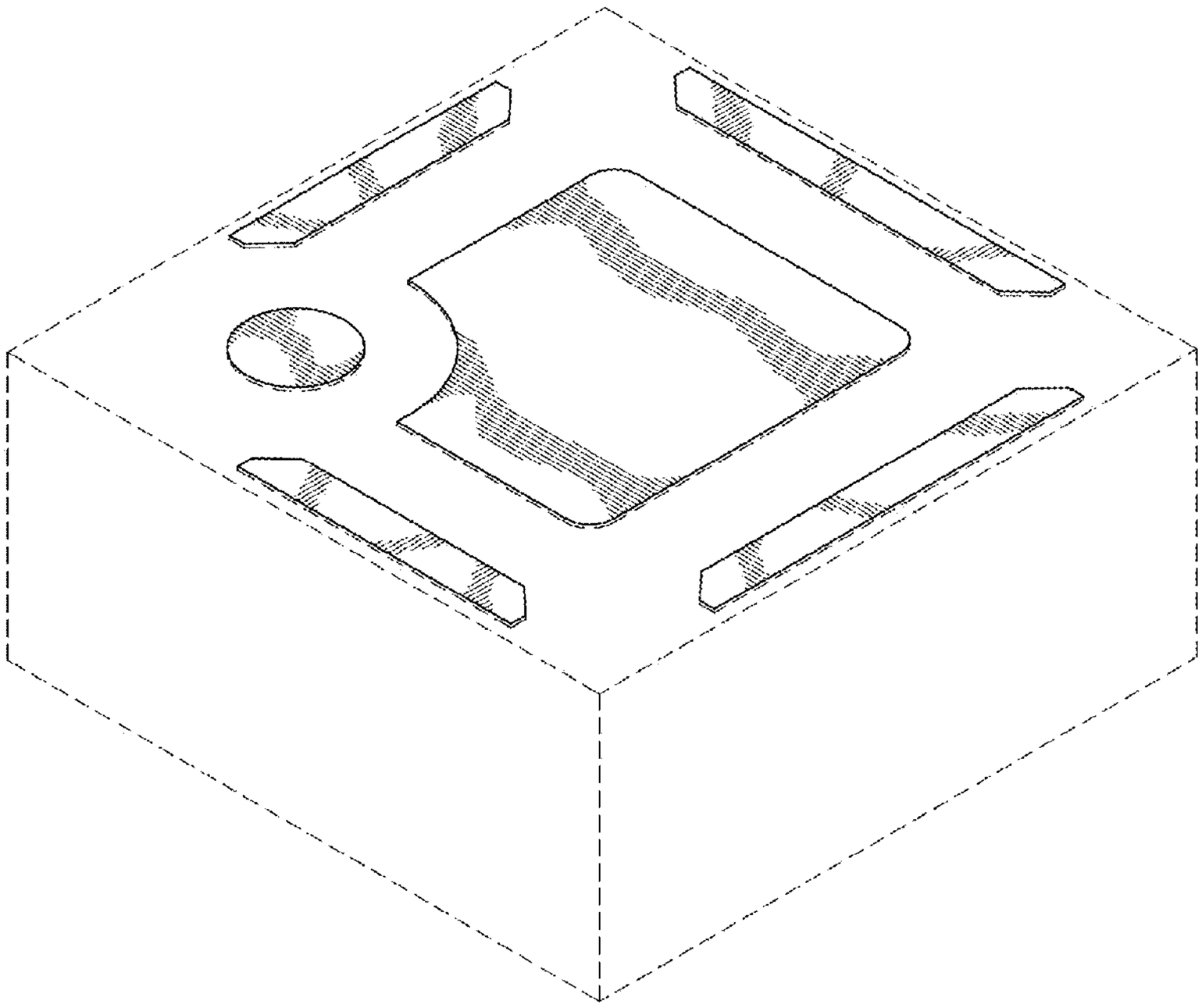

Fig. 2

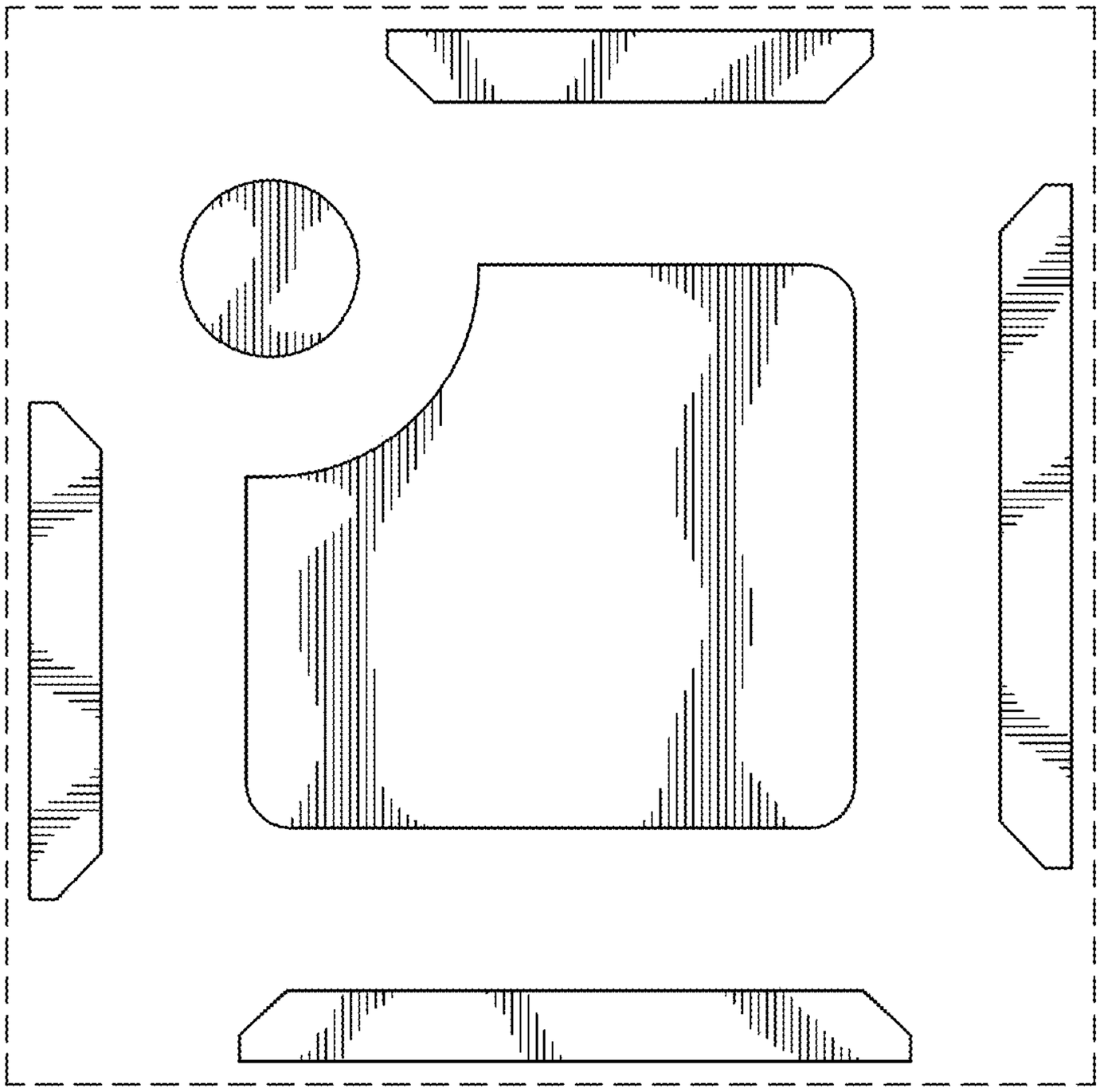

Fig. 3

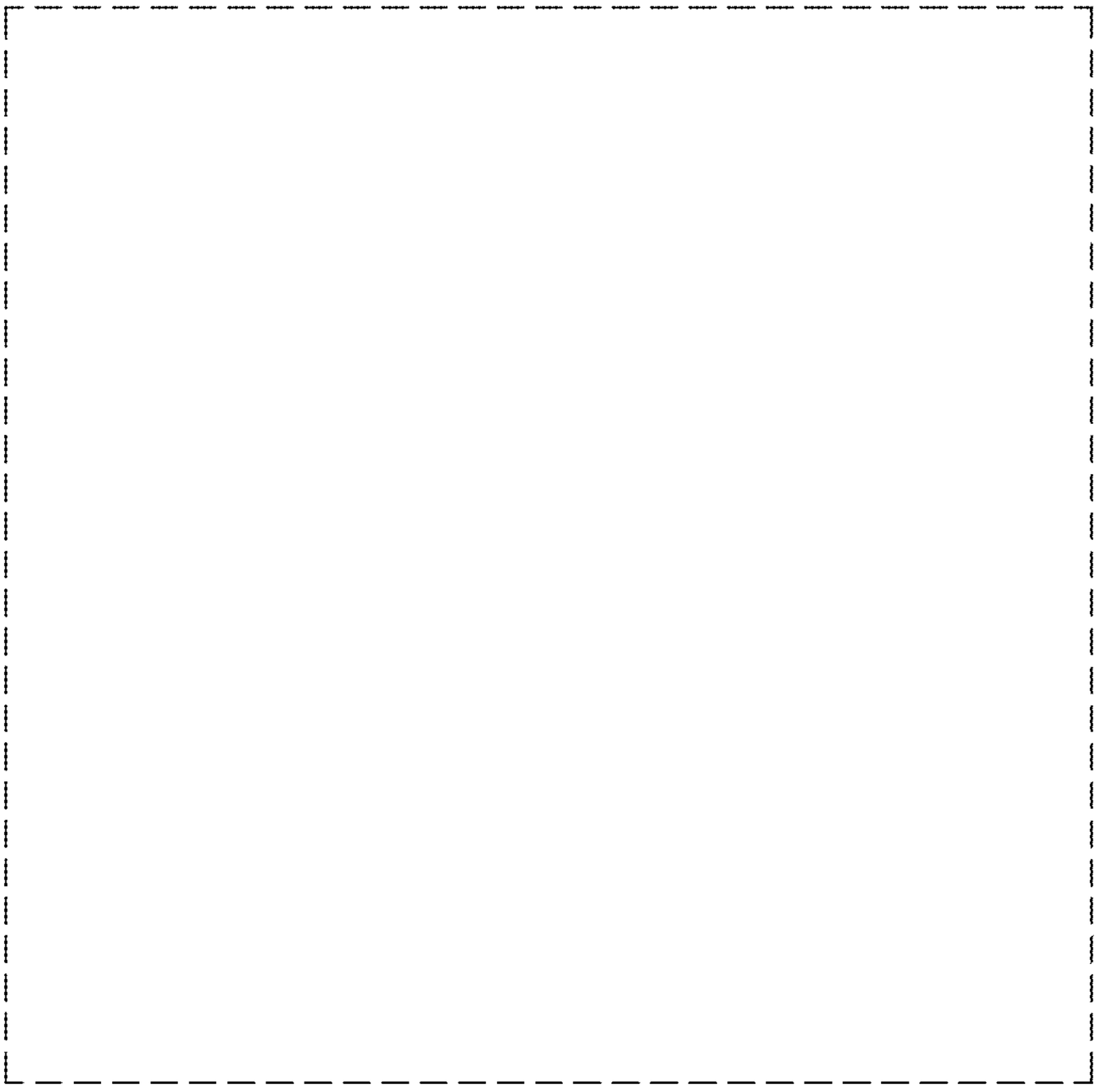

Fig. 4

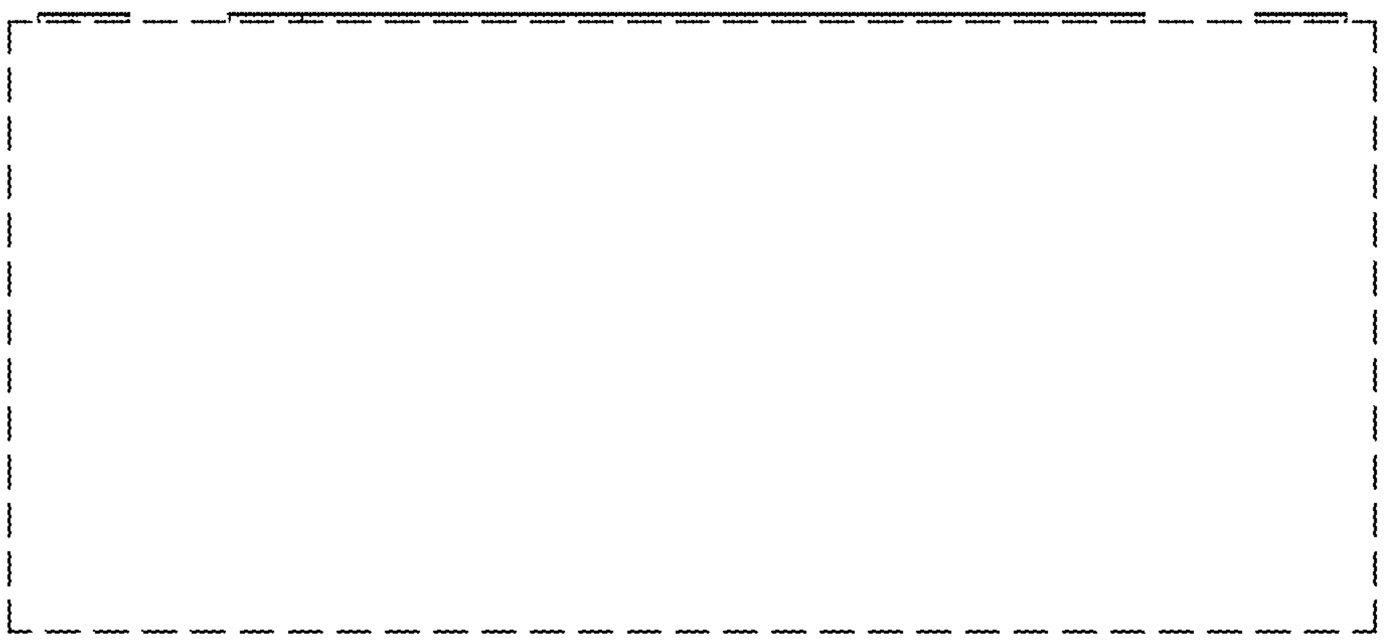

Fig. 5

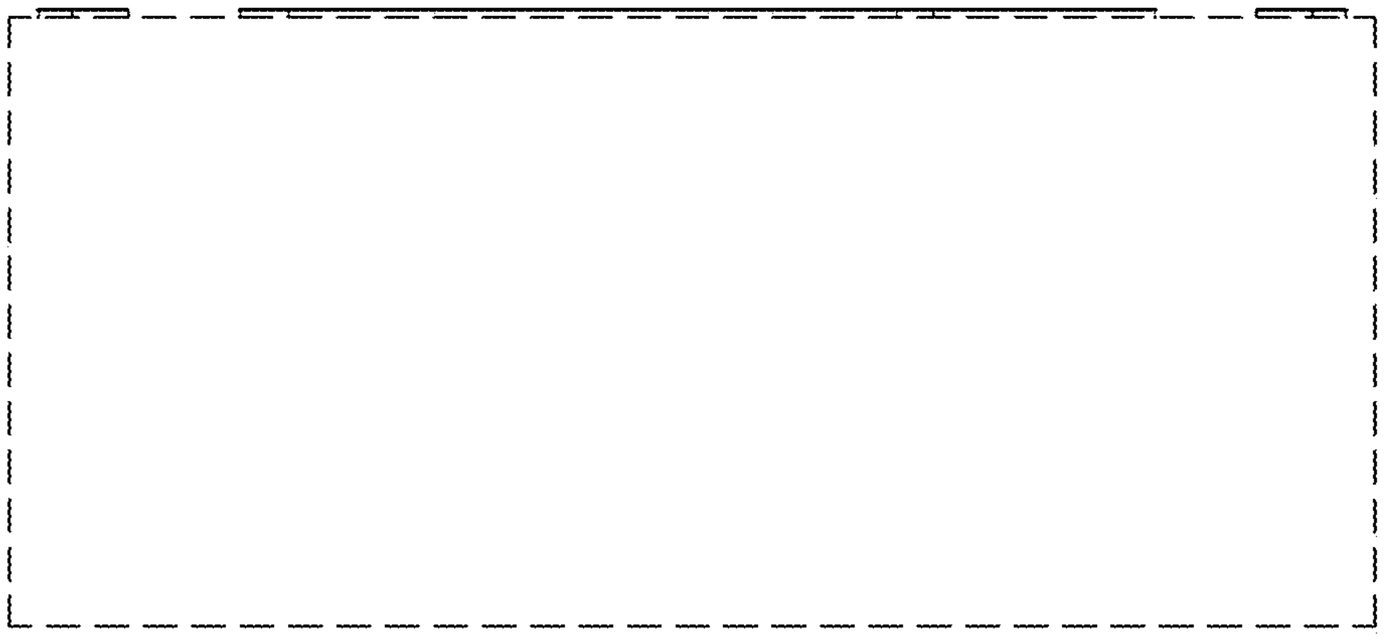

Fig. 6

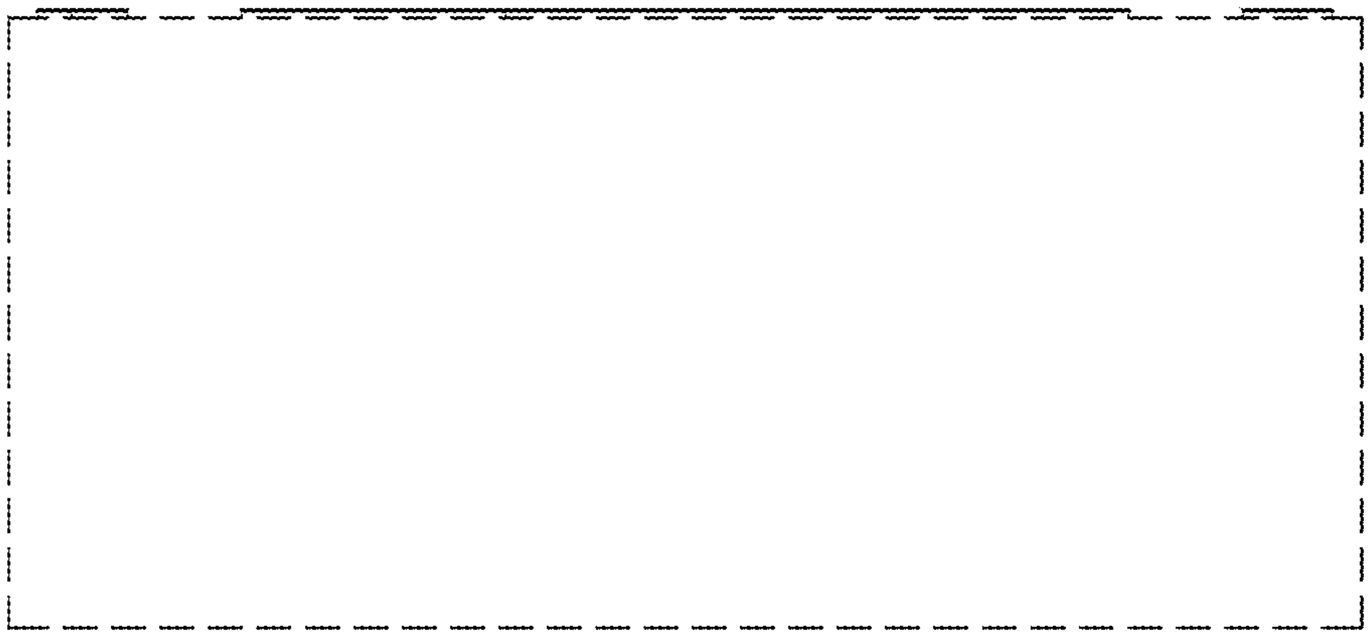

Fig. 7

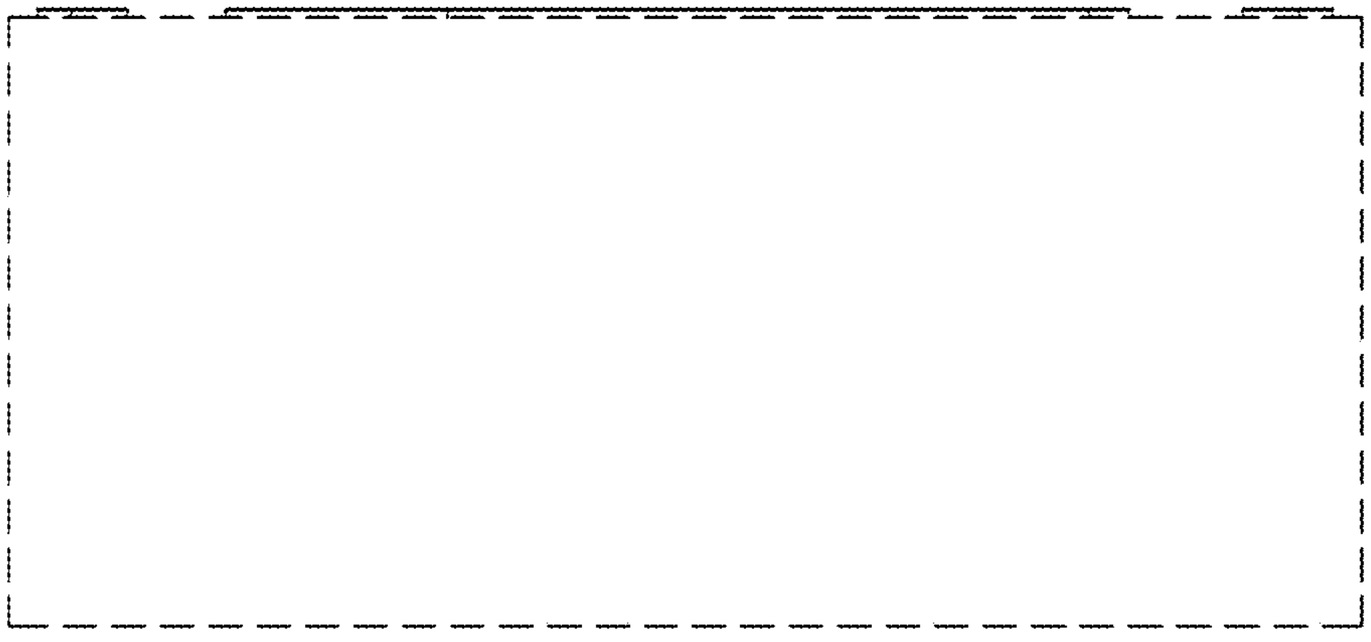

Fig. 8

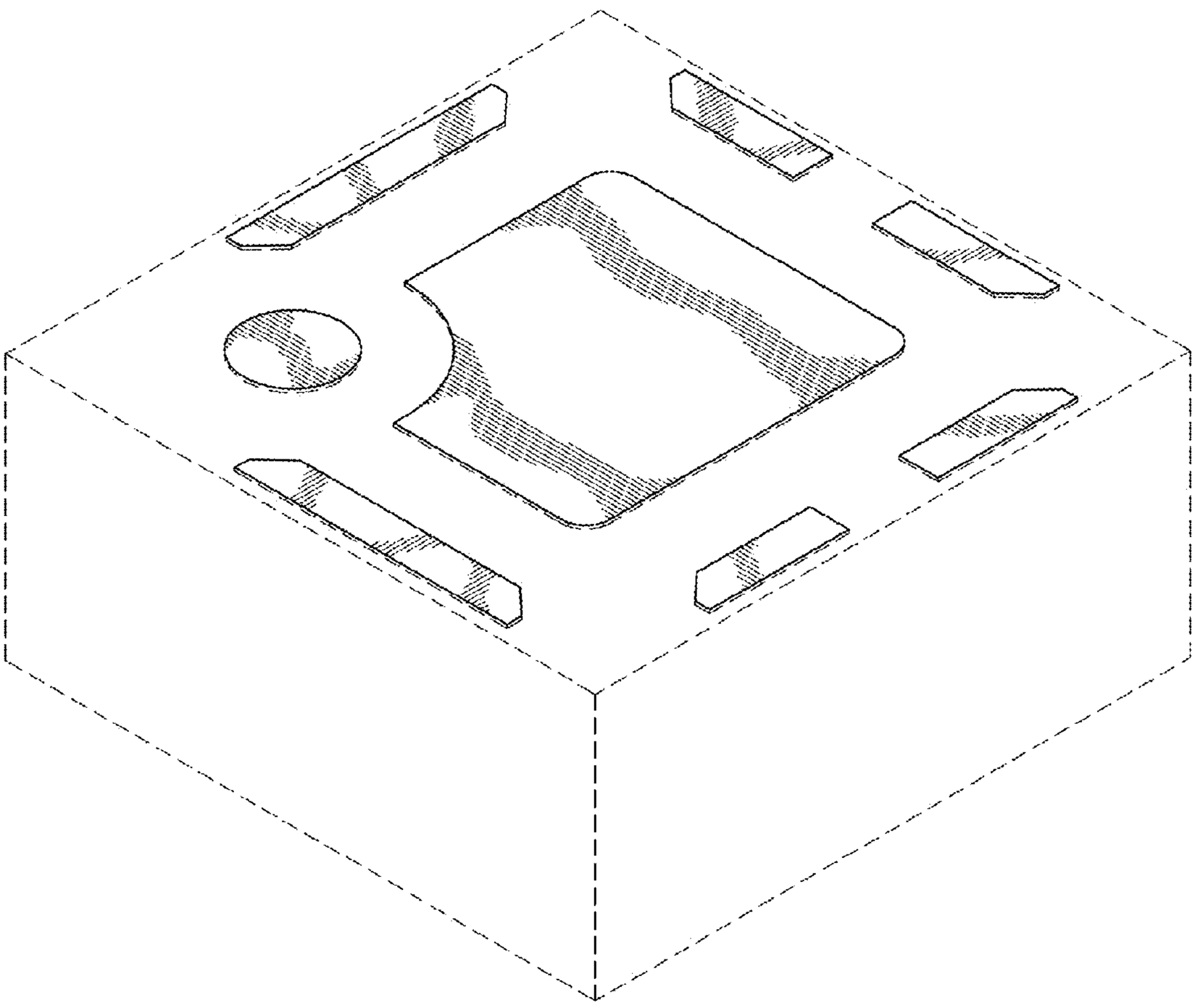

Fig. 9

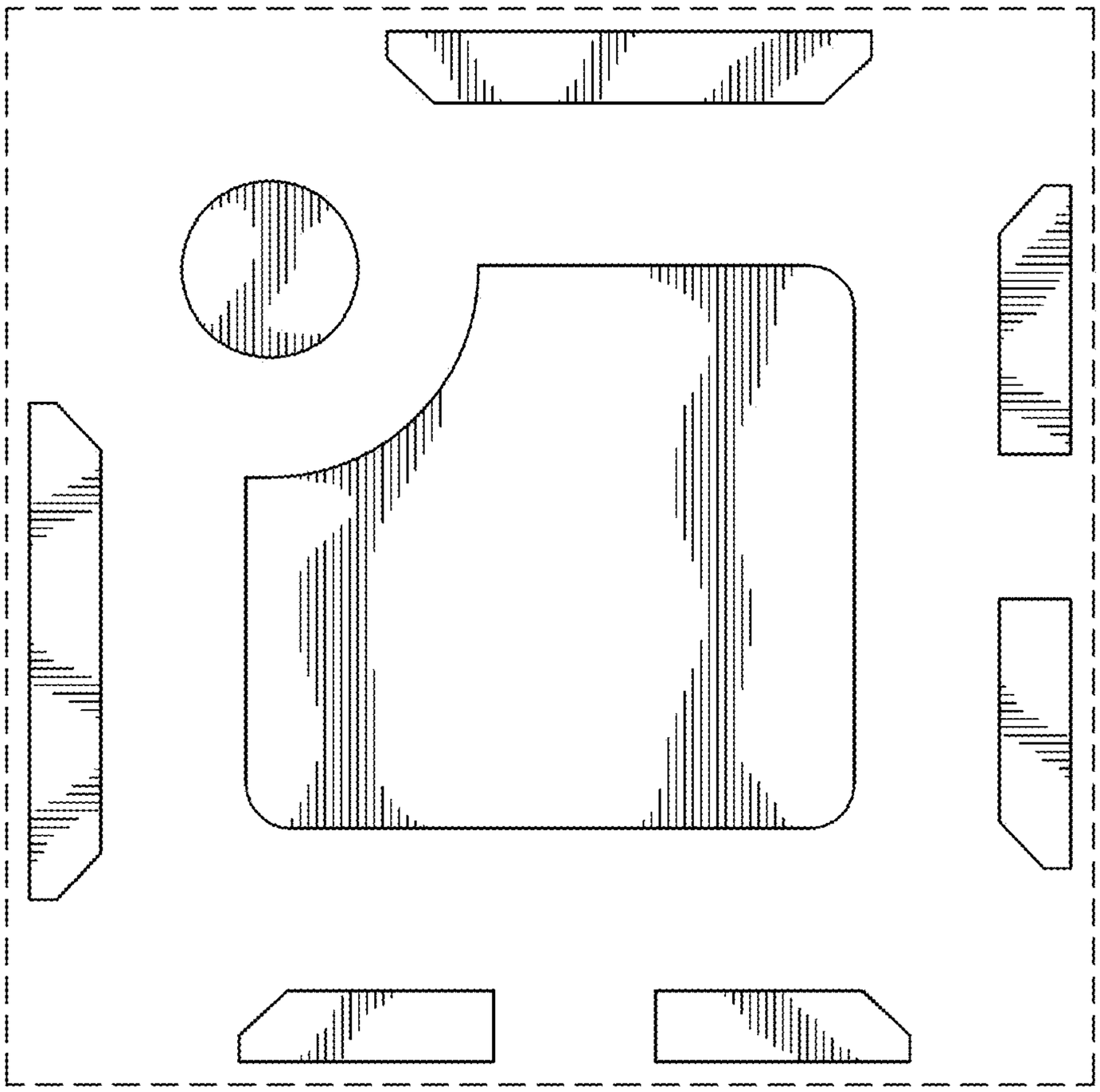

Fig. 10

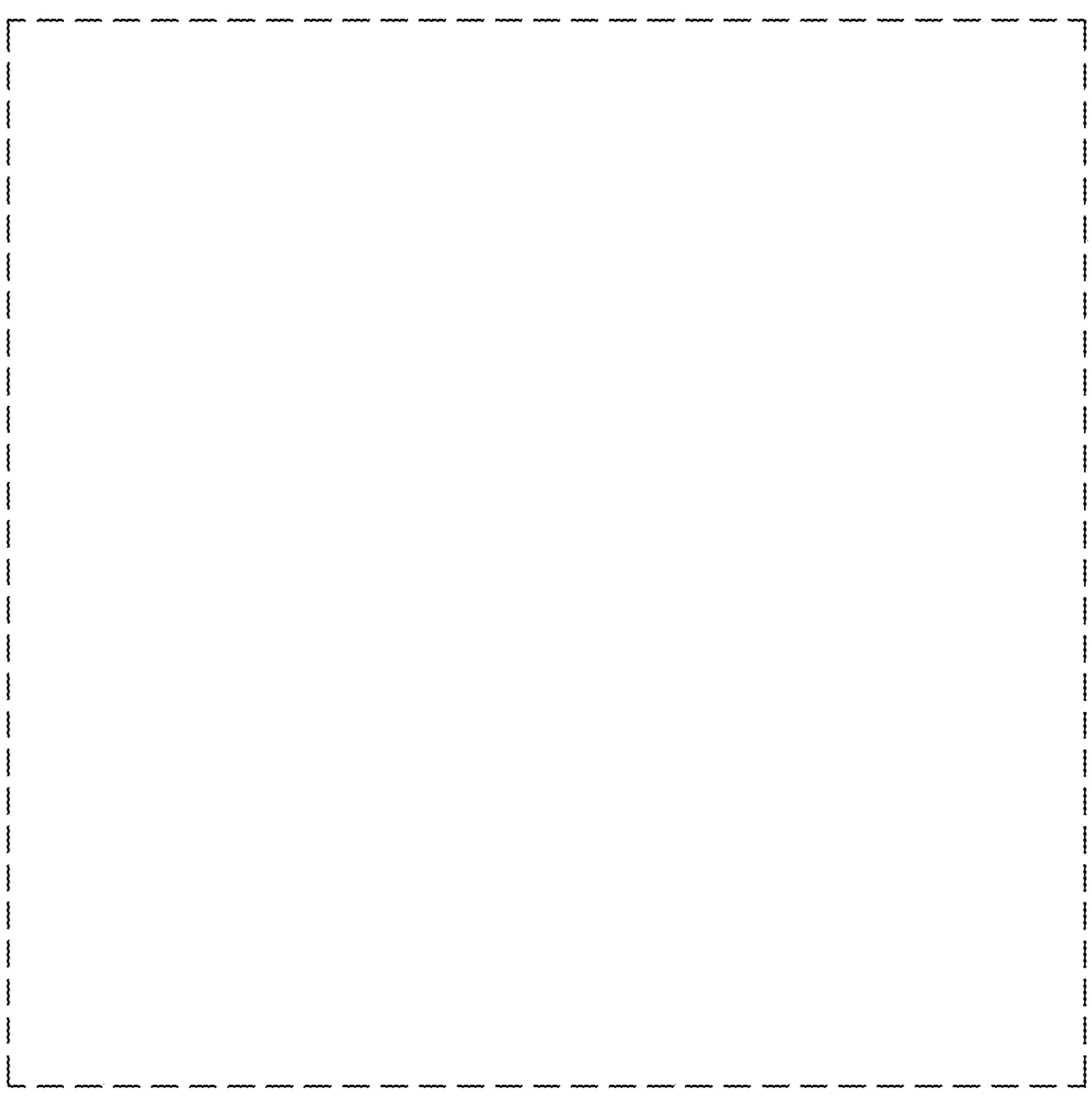

Fig. 11

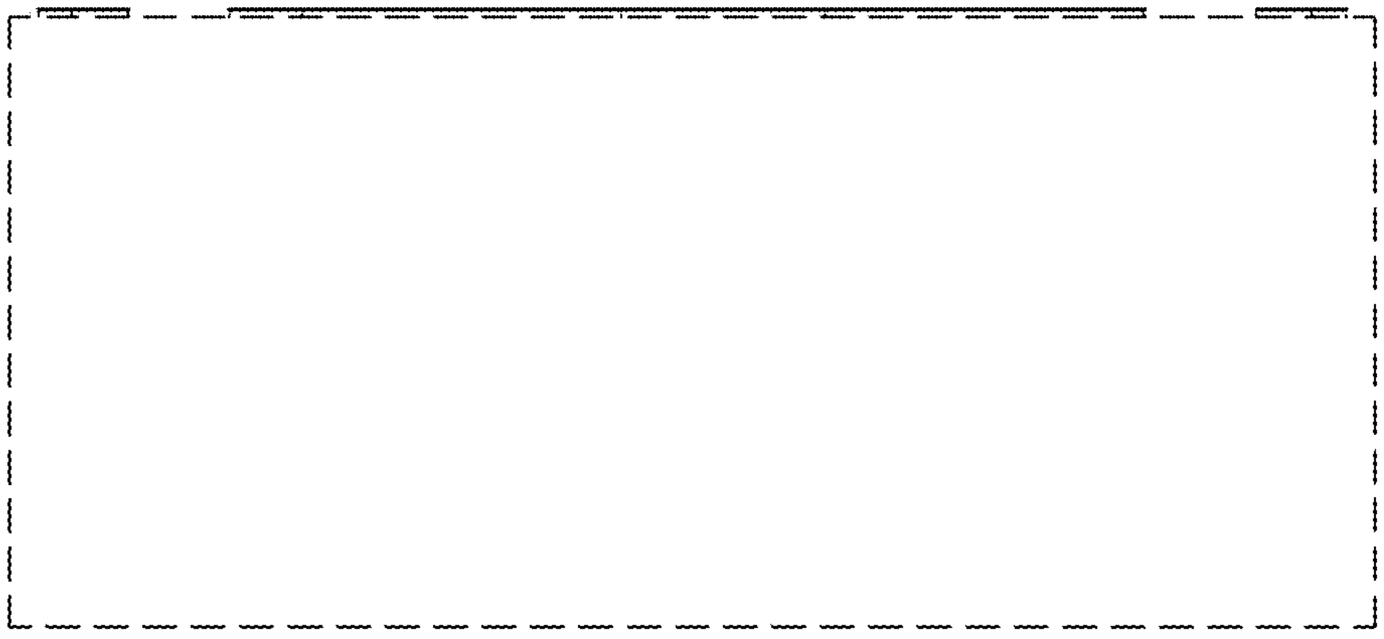

Fig. 12

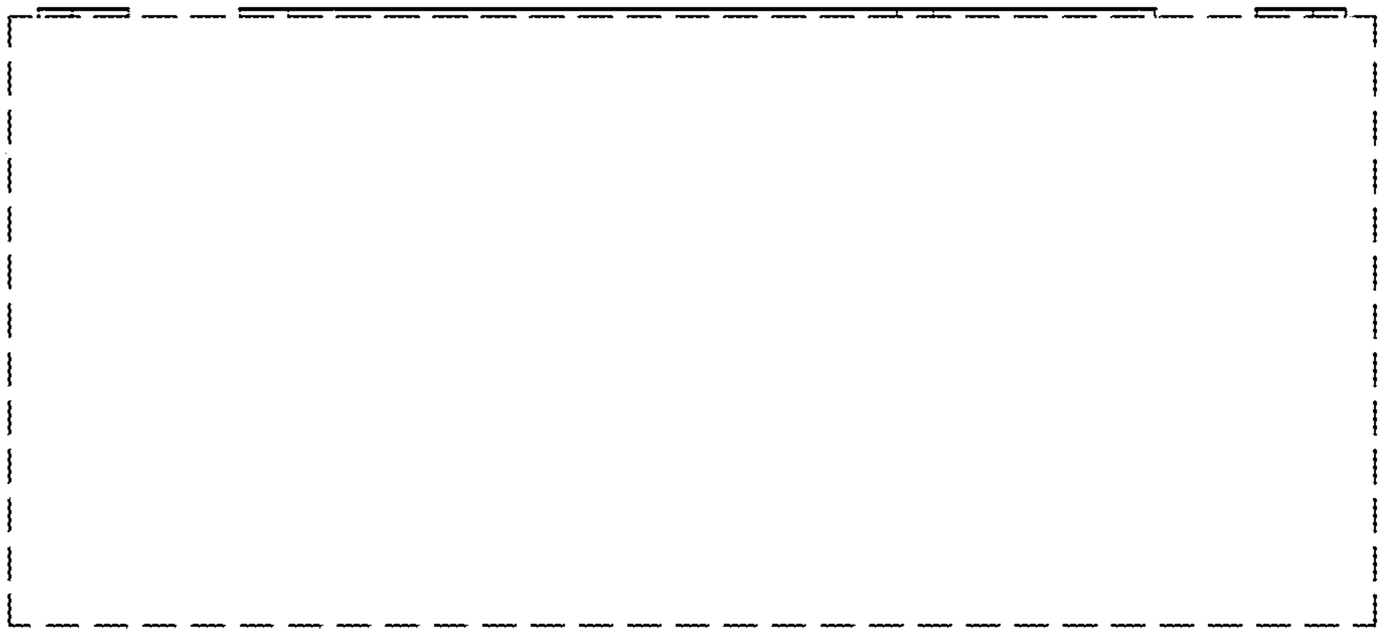

Fig. 13

Fig. 14